

Silicon Diffused Power Transistor

BU508AW

GENERAL DESCRIPTION

High voltage, high-speed switching npn transistors in a plastic envelope, primarily for use in horizontal deflection circuits of colour television receivers.

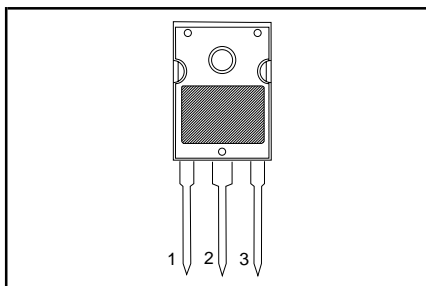
QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V_{CESM}	Collector-emitter voltage peak value	$V_{BE} = 0 \text{ V}$	-	1500	V
V_{CEO}	Collector-emitter voltage (open base)		-	700	V
I_C	Collector current (DC)		-	8	A
I_{CM}	Collector current peak value		-	15	A
P_{tot}	Total power dissipation	$T_{mb} \leq 25 \text{ }^\circ\text{C}$	-	125	W
V_{CESat}	Collector-emitter saturation voltage	$I_C = 4.5 \text{ A}; I_B = 1.6 \text{ A}$	-	1.0	V
I_{Csat}	Collector saturation current	$f = 16 \text{ kHz}$	4.5	-	A
t_f	Fall time	$I_{Csat} = 4.5 \text{ A}; f = 16 \text{ kHz}$	0.7	-	μs

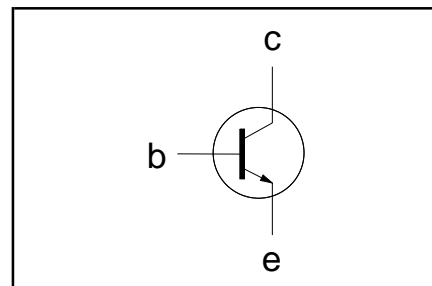
PINNING - SOT429

PIN	DESCRIPTION
1	base
2	collector
3	emitter
tab	collector

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CESM}	Collector-emitter voltage peak value	$V_{BE} = 0 \text{ V}$	-	1500	V
V_{CEO}	Collector-emitter voltage (open base)		-	700	V
I_C	Collector current (DC)		-	8	A
I_{CM}	Collector current peak value		-	15	A
I_B	Base current (DC)		-	4	A
I_{BM}	Base current peak value		-	6	A
P_{tot}	Total power dissipation	$T_{mb} \leq 25 \text{ }^\circ\text{C}$	-	125	W
T_{stg}	Storage temperature		-65	150	$^\circ\text{C}$
T_j	Junction temperature		-	150	$^\circ\text{C}$

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$R_{th\ j-mb}$	Junction to mounting base	-	-	1.0	K/W
$R_{th\ j-a}$	Junction to ambient	in free air	45	-	K/W